

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C
60V	2Ω @ V _{GS} = 4V	400mA
	2.5Ω @ V _{GS} = 2.5V	350mA

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Backlighting
- Power-management functions
- DC-DC converters

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMN62D1LFDQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

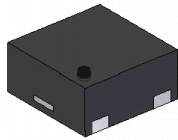
Mechanical Data

- Package: U-DFN1212-3
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

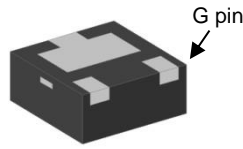
U-DFN1212-3 (Type C)



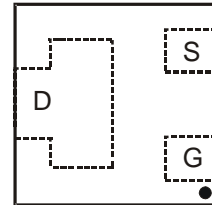
ESD PROTECTED



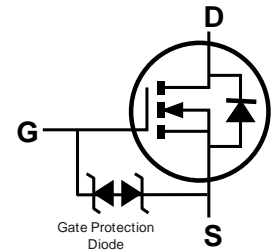
Top View



Bottom View



Pinout Top View



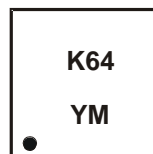
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMN62D1LFDQ-7	U-DFN1212-3 (Type C)	3,000	Tape & Reel
DMN62D1LFDQ-13	U-DFN1212-3 (Type C)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



K64 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: M = 2025)
M = Month (ex: 9 = September)

Date Code Key

Year	2018	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	F	-	M	N	P	R	S	T	U	V	W	X

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 4V	I _D	400 310	mA
Pulsed Drain Current (Note 6)	I _{DM}	1	A

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	0.5	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	237	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±5V, V _{DS} = 0V
		—	—	±500	nA	V _{GS} = ±10V, V _{DS} = 0V
		—	—	±2	μA	V _{GS} = ±15V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.6	—	1	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	0.8	2	Ω	V _{GS} = 4V, I _D = 100mA
		—	1	2.5		V _{GS} = 2.5V, I _D = 50mA
		—	1.4	3		V _{GS} = 1.8V, I _D = 50mA
		—	1.8	—		V _{GS} = 1.5V, I _D = 10mA
		—	—	—		—
Forward Transfer Admittance	Y _{fs}	—	1.8	—	S	V _{DS} = 10V, I _D = 200mA
Diode Forward Voltage	V _{SD}	—	0.8	1.3	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	36	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	4.6	—		
Reverse Transfer Capacitance	C _{rss}	—	3.6	—		
Gate Resistance	R _g	—	59.8	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	0.55	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.08	—		
Gate-Drain Charge	Q _{gd}	—	0.12	—		
Turn-On Delay Time	t _{D(ON)}	—	2.1	—	ns	V _{GS} = 10V, V _{DS} = 30V, R _L = 150Ω, R _G = 25Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	2.8	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	21	—	ns	
Turn-Off Fall Time	t _f	—	13.9	—	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Repetitive rating, pulse width limited by junction temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

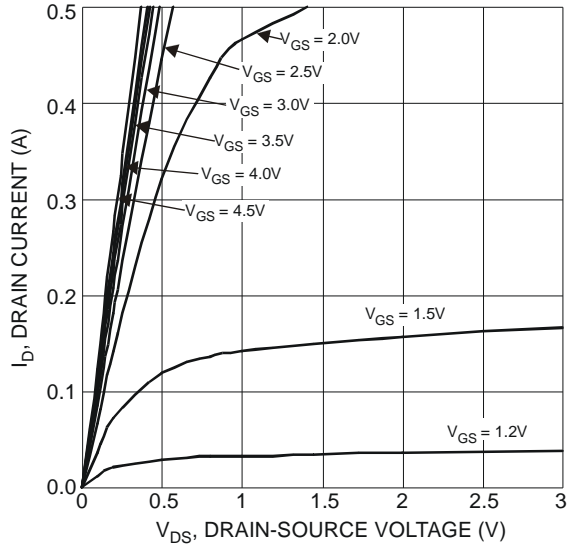


Figure 1 Typical Output Characteristics

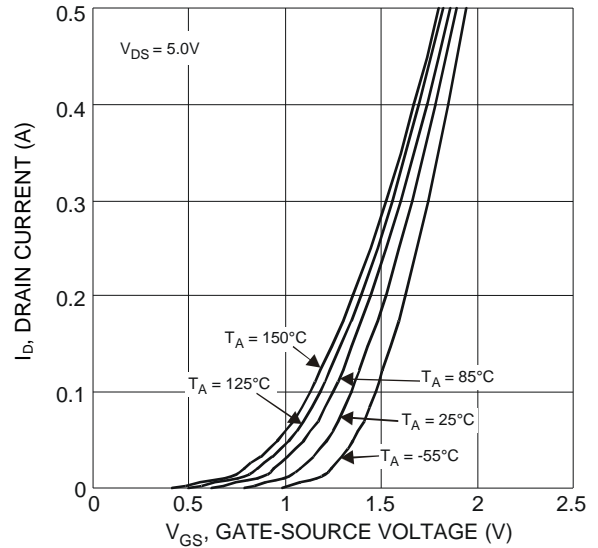


Figure 2 Typical Transfer Characteristics

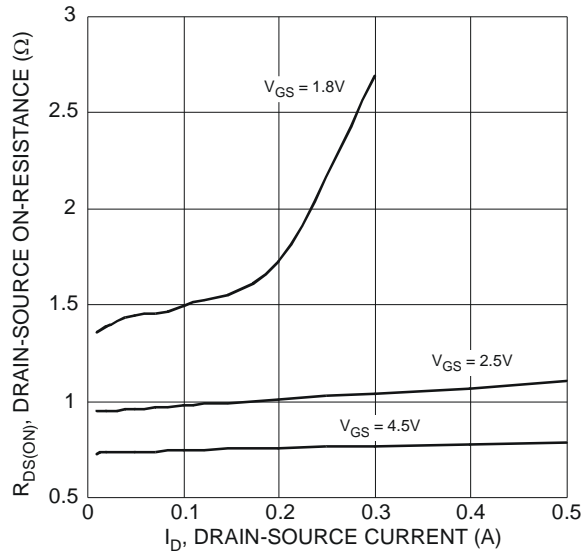


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

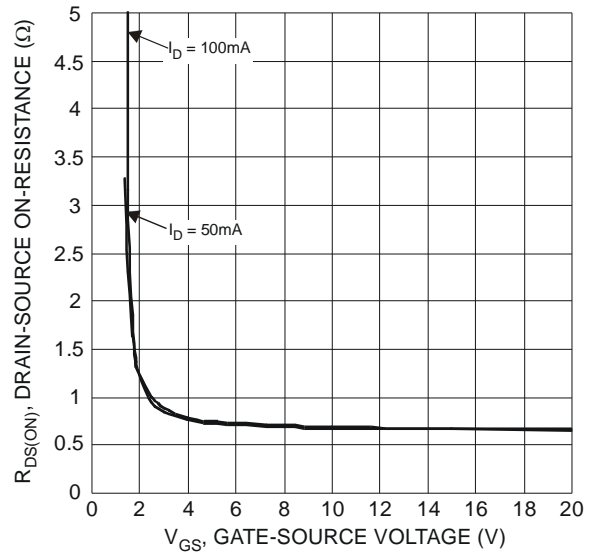


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

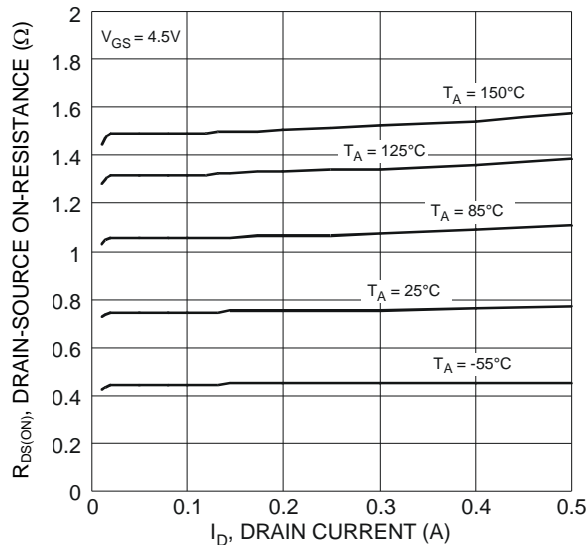


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

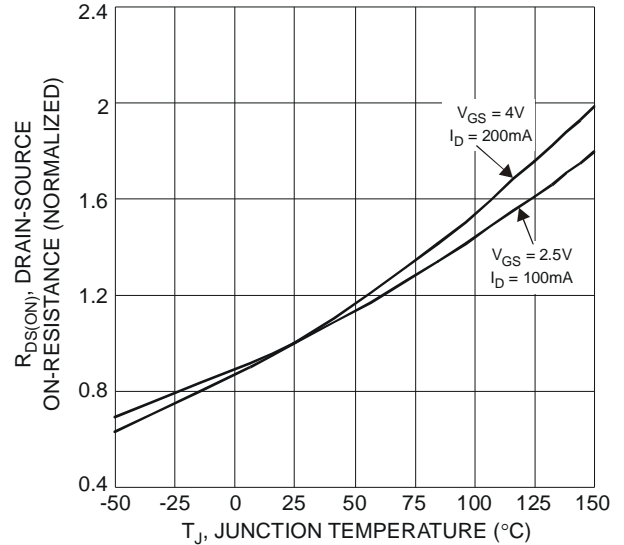
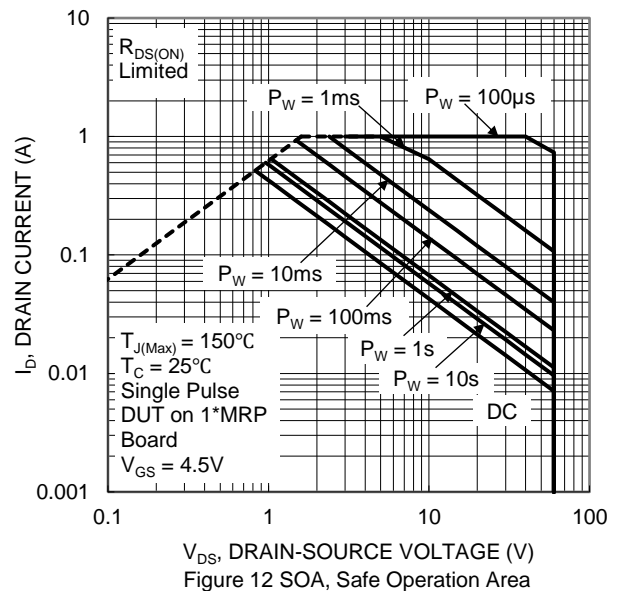
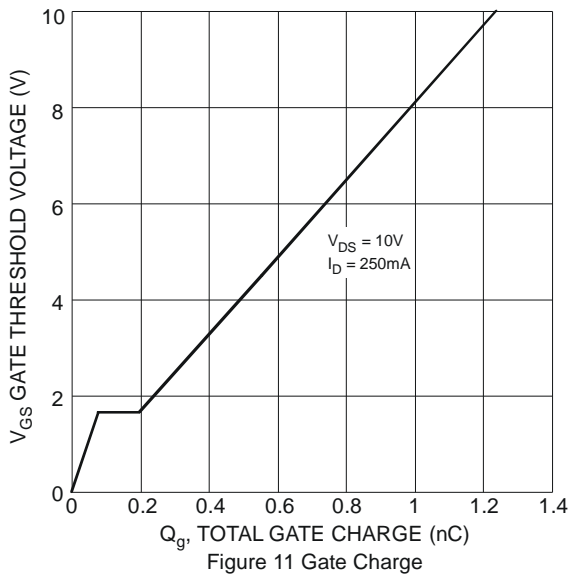
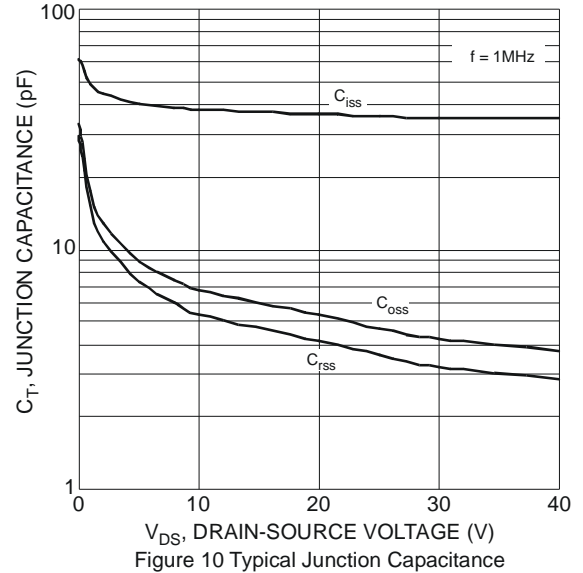
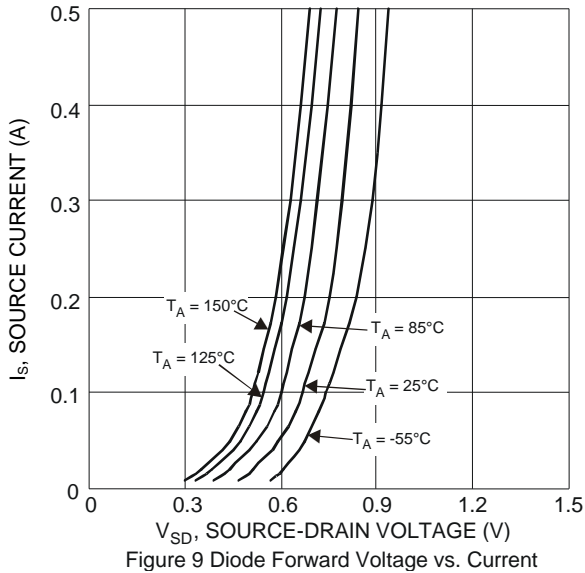
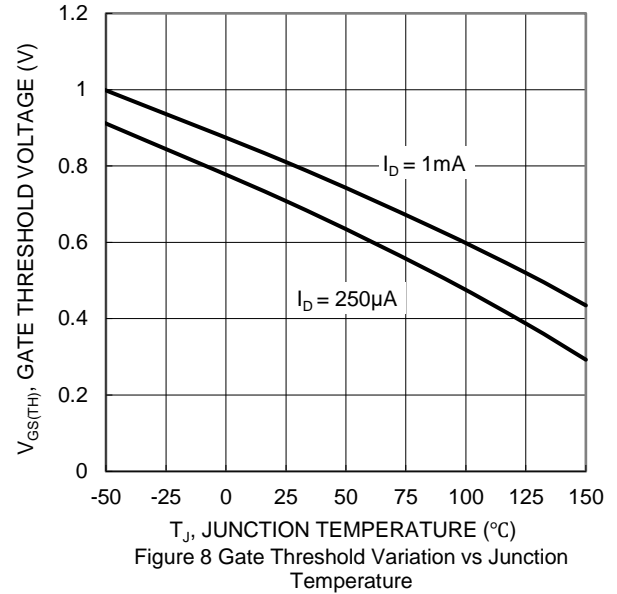
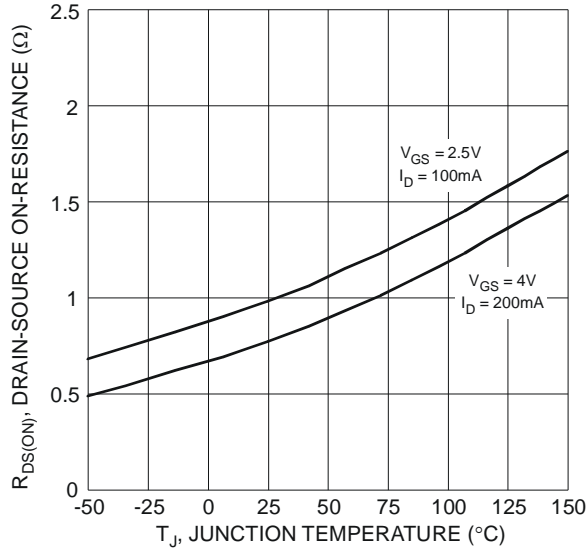


Figure 6 On-Resistance Variation with Temperature



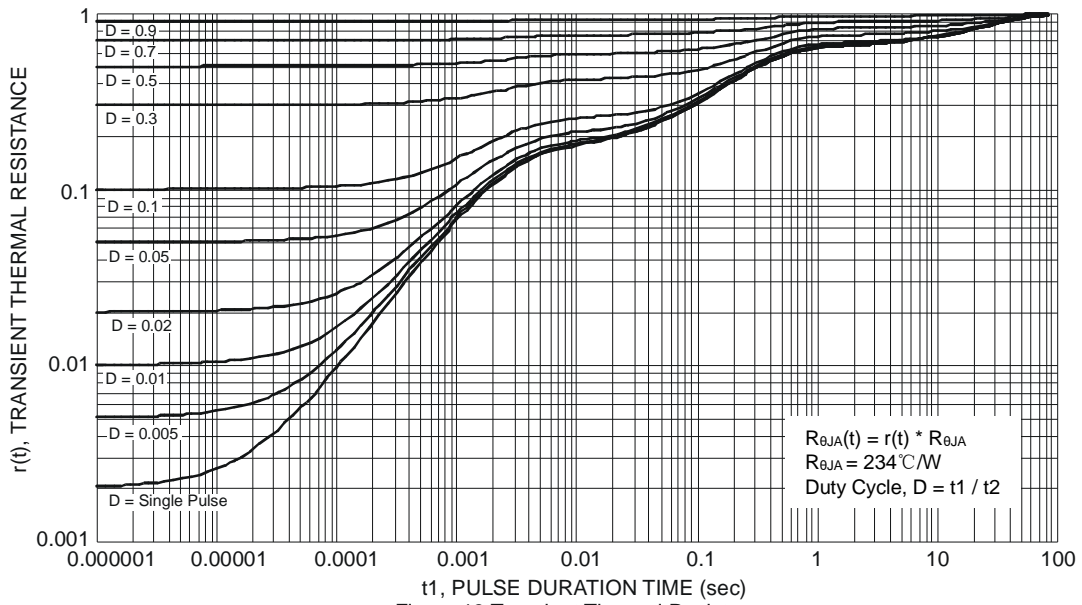
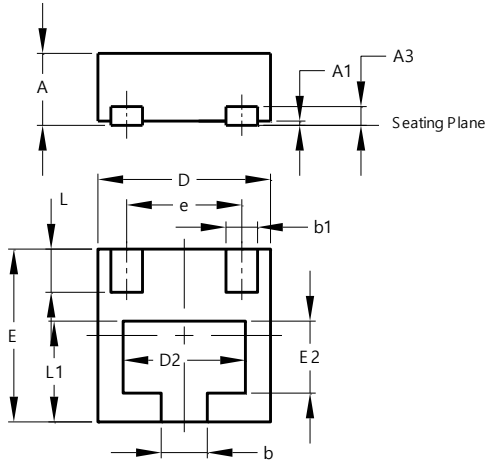


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN1212-3 (Type C)

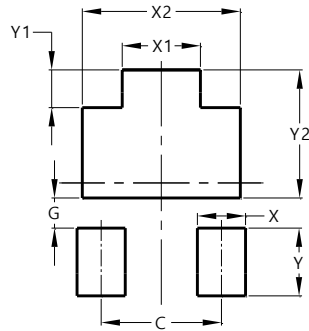


U-DFN1212-3 Type C			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	-	-	0.13
b	0.27	0.37	0.32
b1	0.17	0.27	0.22
D	1.15	1.25	1.20
D2	0.75	0.95	0.85
e	-	-	0.80
E	1.15	1.25	1.20
E2	0.40	0.60	0.50
L	0.25	0.35	0.30
L1	0.65	0.75	0.70
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN1212-3 (Type C)



Dimensions	Value (in mm)
C	0.800
G	0.200
X	0.320
X1	0.520
X2	1.050
Y	0.450
Y1	0.250
Y2	0.850

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